

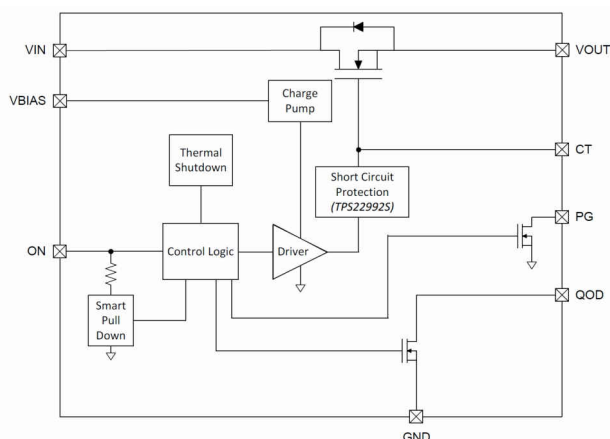
TPS22992x 5V、8.7mΩ、6A ロード・スイッチ、可変立ち上がり時間

1 特長

- 動作入力電圧範囲 (V_{IN}):
 - TPS22992: 0.1V~5.5V
 - TPS22992S: 1V~5.5V
- バイアス電源電圧 (V_{BIAS}): 1.5V~5.5V
- 最大連続電流: 6A
- オン抵抗 (R_{ON}): 8.7mΩ (標準値)
- 調整可能なスルーレート制御
- 可変クイック出力放電 (QOD)
- オープン・ドレインのパワー・グッド (PG) 信号
- 低消費電力:
 - オン状態 (I_Q): 10μA (標準値, TPS22992)
 - オン状態 (I_Q): 30μA (標準値, TPS22992S)
 - オフ状態 (I_{SD}): 0.1μA (標準値)
- 短絡保護 (TPS22992S のみ)
- サーマル・シャットダウン
- ON ピンのスマート・プルダウン ($R_{PD,ON}$)
 - $ON \geq V_{IH}$ (I_{ON}): 25nA (標準値)
 - $ON \leq V_{IL}$ ($R_{PD,ON}$): 500kΩ (標準値)

2 アプリケーション

- データ・ストレージ
- PC / ノート PC
- 産業用 PC
- 光学モジュール



TPS22992x のブロック図

3 概要

TPS22992x 製品ファミリーは 2 つのデバイス (TPS22992、TPS22992S) で構成されています。各デバイスは、最大 5.5V/6A のアプリケーションの電力密度を最大限に高めるように設計された 8.7mΩ パワー MOSFET 内蔵シングル・チャネル・ロード・スイッチです。立ち上がり時間を設定できるため、柔軟な電源シーケンスが可能であり、大容量負荷への突入電流を最小化できます。

このスイッチは 1 本のイネーブル・ピン (ON) で制御されます。このイネーブル・ピンは低電圧の GPIO 信号 ($V_{IH} = 0.8V$) と直接接続できます。TPS22992x デバイスは、スイッチをオフにした際に出力を素早く放電させるためのオプションの QOD ピンを持っており、その出力立ち下がり時間 (t_{FALL}) は外付け抵抗で調整できます。本デバイスは、メイン MOSFET が完全にオンしていることを示すパワー・グッド (PG) 信号を持っています。この PG 信号を使って下流の負荷を有効にできます。

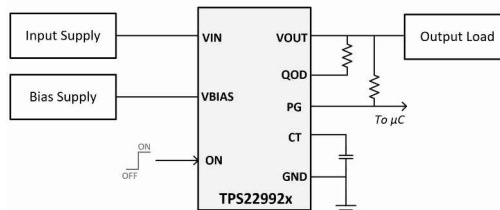
両 TPS22992x デバイスは、高温環境での保護を確保するためサーマル・シャットダウン機能を備えています。TPS22992S デバイスは過電流保護機能も内蔵しており、動作中または起動時に出力がグランドに短絡した場合のデバイスへの損傷を防止します。

省スペース型アプリケーション向けに、TPS22992x デバイスは 1.25 × 1.25mm、0.4mm ピッチの 8 ピン WQFN パッケージで供給されます。より広いピン・ピッチが必要な場合に備えて、TPS22992 デバイスは 1.5 × 1.25mm、0.5mm ピッチの 8 ピン WQFN パッケージでも供給されます。どちらのデバイスも、-40°C~+125°C の周囲温度範囲で動作が規定されています。

製品情報

部品番号	パッケージ ⁽¹⁾	本体サイズ (公称)
TPS22992	WQFN - 8 (RXP)	1.5mm × 1.25mm
TPS22992S	WQFN - 8 (RXN)	1.25mm × 1.25mm

- (1) 利用可能なすべてのパッケージについては、このデータシートの末尾にある注文情報を参照してください。



TPS2299x を使った電源シーケンス



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4 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision * (July 2021) to Revision A (December 2021)	Page
• ステータスを「事前情報」から「量産データ」に変更.....	1

5 Device Comparison Table

DEVICE	VIN RANGE	R _{ON} AT VBIAS = 5 V	QUIESCENT CURRENT	PACKAGE DIMENSIONS	PIN PITCH
TPS22992RXP	0.1 V to 5.5 V	8.7 mΩ	10 μA	1.5 mm x 1.25 mm	0.5 mm
TPS22992SRXN	1 V to 5.5 V	8.7 mΩ	40 μA	1.25 mm x 1.25 mm	0.4 mm

6 Pin Configuration and Functions

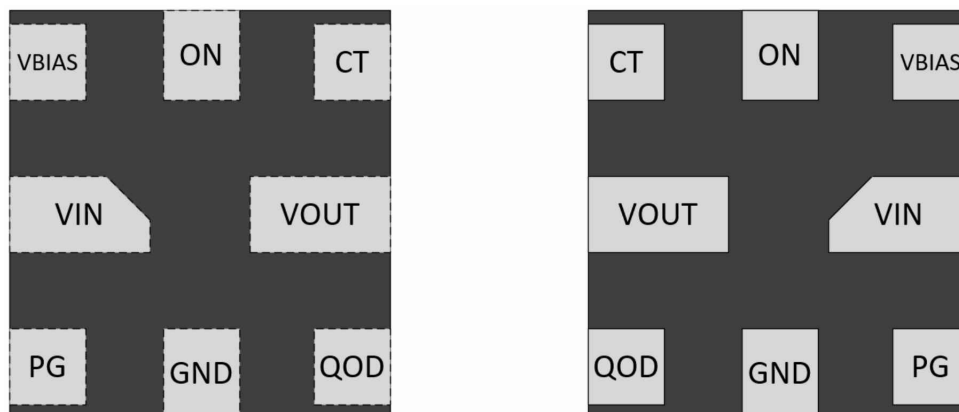


图 6-1. TPS22992x Pinout (Top View Left, Bottom View Right)

表 6-1. Pin Functions

PIN		I/O ⁽¹⁾	DESCRIPTION
NAME	NO.		
VBIAS	1	I	Bias voltage
VIN	2	I	Input voltage
PG	3	O	Open drain power good signal, asserted high when the output is full load ready
GND	4	—	Device ground
QOD	5	—	Quick output discharge pin
VOUT	6	O	Output voltage
CT	7	O	Timing pin, can control the slew rate of the output through a capacitor to GND
ON	8	I	Enable pin

(1) I = Input, O = Output, I/O = Input or Output, G = Ground, P = Power.

7 Specifications

7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT
V _{IN}	Input Voltage	−0.3	6	V
V _{BIAS}	Bias Voltage	−0.3	6	V
V _{ON} , V _{PG} , V _{QOD}	Control Pin Voltage	−0.3	6	V
V _{CT}	CT Pin Voltage		15	V
I _{MAX}	Maximum Current		6	A
T _J	Junction temperature		Internally Limited	°C
T _{stg}	Storage temperature	−65	150	°C

- (1) Stresses beyond those listed under *Absolute Maximum Rating* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Condition*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

7.2 ESD Ratings

			VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±2000	V
		Charged device model (CDM), per ANSI/ESDA/JEDEC JS-002 ⁽²⁾	±1000	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
 (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V _{IN}	TPS22992 Input Voltage	0.1		V _{BIAS}	V
	TPS22992S Input Voltage	1		V _{BIAS}	V
V _{BIAS}	Bias Voltage	1.5		5.5	V
V _{IH}	ON Pin High Voltage Range	0.8		5.5	V
V _{IL}	ON Pin Low Voltage Range	0		0.35	V
V _{PG} , V _{QOD}	Control Pin Voltage	0		5.5	V
T _A	Ambient Temperature	−40		125	°C

7.4 Thermal Information

THERMAL METRIC ⁽¹⁾		TPS22992		UNIT
		RXP (WQFN)	RXN (WQFN)	
		8 PINS	8 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	110.0	119.4	°C/W
Ψ _{JT}	Junction-to-top characterization parameter	6.8	6.9	°C/W
Y _{JB}	Junction-to-board characterization parameter	36.6	35.2	°C/W

- (1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) application report.

7.5 Electrical Characteristics (VBIAS = 5 V)

Over operating free-air temperature range (unless otherwise noted). Typical values are at $T_A = 25^\circ\text{C}$ and $V_{IN} = 5\text{V}$.

PARAMETER		TEST CONDITIONS	T _A	MIN	TYP	MAX	UNIT
Power Consumption							
I _{SD,VBIAS}	VBIAS Shutdown Current	ON = 0 V	25°C	0.1			uA
			–40°C to 85°C	0.25		uA	
			–40°C to 125°C	0.36		uA	
I _{Q,VBIAS}	VBIAS Quiescent Current (TPS22992)	ON > V _{IH}	25°C	10			uA
			–40°C to 85°C	16		uA	
			–40°C to 125°C	20		uA	
I _{Q,VBIAS}	VBIAS Quiescent Current (TPS22992S)	ON > V _{IH}	25°C	30			uA
			–40°C to 85°C	45		uA	
			–40°C to 125°C	50		uA	
I _{SD,VIN}	VIN Shutdown Current	ON = 0 V	–40°C to 125°C	0.1			uA
I _{ON}	ON pin leakage	ON = VBIAS	–40°C to 125°C	0.1			uA
Performance							
R _{ON}	On-Resistance	VIN = 5 V	25°C	8.7			mΩ
			–40°C to 85°C	12		mΩ	
			–40°C to 125°C	14		mΩ	
		VIN = 3.3 V	25°C	8.7			mΩ
			–40°C to 85°C	12		mΩ	
			–40°C to 125°C	15		mΩ	
		VIN = 1.8 V	25°C	8.7			mΩ
			–40°C to 85°C	12		mΩ	
			–40°C to 125°C	14		mΩ	
		VIN = 1.2 V	25°C	8.7			mΩ
			–40°C to 85°C	12		mΩ	
			–40°C to 125°C	14		mΩ	
		VIN = 0.8 V	25°C	8.7			mΩ
			–40°C to 85°C	12		mΩ	
			–40°C to 125°C	14		mΩ	
V _{OL,PG}	Power Good V _{OL}	I _{PG} = 1 mA	–40°C to 125°C	0.2			V
R _{PD,ON}	Smart Pull Down Resistance	ON < V _{IL}	25°C	500			kΩ
			–40°C to 125°C	1000		kΩ	
R _{QOD}	QOD Resistance	ON < V _{IL}	25°C	25			Ω
R _{QOD}			–40°C to 125°C	100		Ω	
Protection							
I _{SC,H}	Short Circuit Current Limit (High)	V _{OUT} ≤ V _{IN} - 1.5 V	–40°C to 125°C	11			A
I _{SC,L}	Short Circuit Current Limit (Low)	V _{OUT} ≤ V _{SC}	–40°C to 125°C	1.5			A
t _{SC}	Short Circuit Response Time	V _{IN} = 1 V to 5.5 V	–40°C to 125°C	5			μs
V _{SC}	Short Circuit Detection Threshold	VOUT voltage level, rising	–40°C to 125°C	0.45			V
		VOUT voltage level, falling	–40°C to 125°C	0.35		V	
TSD	Thermal Shutdown		-	170			°C
TSD _{HYS}	Thermal Shutdown Hysteresis		-	20			°C

7.6 Electrical Characteristics (VBIAS = 3.3 V)

over operating free-air temperature range (unless otherwise noted). Typical values are at $T_A = 25^\circ\text{C}$ and $V_{IN} = 3.3\text{V}$.

PARAMETER		TEST CONDITIONS	T _A	MIN	TYP	MAX	UNIT
Power Consumption							
I _{SD,VBIAS}	VBIAS Shutdown Current	ON = 0 V	25°C	0.1			uA
			–40°C to 85°C	0.2		uA	
			–40°C to 125°C	0.27		uA	
I _{Q,VBIAS}	VBIAS Quiescent Current (TPS22992)	ON > V _{IH}	25°C	10			uA
			–40°C to 85°C	15		uA	
			–40°C to 125°C	16		uA	
I _{Q,VBIAS}	VBIAS Quiescent Current (TPS22992S)	ON > V _{IH}	25°C	26			uA
			–40°C to 85°C	42		uA	
			–40°C to 125°C	45		uA	
I _{SD,VIN}	VIN Shutdown Current	ON = 0 V	–40°C to 125°C	0.1			uA
I _{ON}	ON pin leakage	ON = VBIAS	–40°C to 125°C	0.1			uA
Performance							
R _{ON}	On-Resistance	VIN = 3.3 V	25°C	8.7			mΩ
			–40°C to 85°C	12		mΩ	
			–40°C to 125°C	15		mΩ	
		VIN = 1.8 V	25°C	8.7			mΩ
			–40°C to 85°C	12		mΩ	
			–40°C to 125°C	15		mΩ	
		VIN = 1.2 V	25°C	8.7			mΩ
			–40°C to 85°C	12		mΩ	
			–40°C to 125°C	15		mΩ	
		VIN = 0.8 V	25°C	8.7			mΩ
			–40°C to 85°C	12		mΩ	
			–40°C to 125°C	15		mΩ	
V _{OL,PG}	Power Good V _{OL}	I _{PG} = 1 mA	–40°C to 125°C	0.2			V
R _{PD,ON}	Smart Pull Down Resistance	ON < V _{IL}	25°C	500			kΩ
			–40°C to 125°C	1000		kΩ	
R _{QOD}	QOD Resistance	ON < V _{IL}	25°C	25			Ω
			–40°C to 125°C	100		Ω	
Protection							
I _{SC,H}	Short Circuit Current Limit (High)	V _{OUT} ≤ V _{IN} - 1.5 V	–40°C to 125°C	10			A
I _{SC,L}	Short Circuit Current Limit (Low)	V _{OUT} ≤ V _{SC}	–40°C to 125°C	1.5			A
t _{SC}	Short Circuit Response Time	V _{IN} = 1 V to 5.5 V	–40°C to 125°C	5			μs
V _{SC}	Short Circuit Detection Threshold	VOUT voltage level, rising	–40°C to 125°C	0.45			V
		VOUT voltage level, falling	–40°C to 125°C	0.35		V	
TSD	Thermal Shutdown		-	170			°C
TSD _{HYS}	Thermal Shutdown Hysteresis		-	20			°C

7.7 Electrical Characteristics (VBIAS = 1.5 V)

Over operating free-air temperature range (unless otherwise noted). Typical values are at $T_A = 25^\circ\text{C}$ and $V_{IN} = 1.5\text{V}$.

PARAMETER		TEST CONDITIONS	T_A	MIN	TYP	MAX	UNIT
Power Consumption							

7.7 Electrical Characteristics (VBIAS = 1.5 V) (continued)

Over operating free-air temperature range (unless otherwise noted). Typical values are at $T_A = 25^\circ\text{C}$ and $V_{IN} = 1.5\text{V}$.

PARAMETER		TEST CONDITIONS	T _A	MIN	TYP	MAX	UNIT
I _{SD,VBIAS}	VBIAS Shutdown Current	ON = 0 V	25°C	0.1			uA
			–40°C to 85°C	0.2		uA	
			–40°C to 125°C	0.25		uA	
I _{Q,VBIAS}	VBIAS Quiescent Current (TPS22992)	ON > V _{IH}	25°C	8			uA
			–40°C to 85°C	12		uA	
			–40°C to 125°C	14		uA	
I _{Q,VBIAS}	VBIAS Quiescent Current (TPS22992S)	ON > V _{IH}	25°C	22			uA
			–40°C to 85°C	29		uA	
			–40°C to 125°C	31		uA	
I _{SD,VIN}	VIN Shutdown Current	ON = 0 V	–40°C to 125°C	0.1			uA
I _{ON}	ON pin leakage	ON = VBIAS	–40°C to 125°C	0.1			uA
Performance							
R _{ON}	On-Resistance	VIN = 1.5 V	25°C	12.7			mΩ
			–40°C to 85°C	21		mΩ	
			–40°C to 125°C	27		mΩ	
		VIN = 1.2 V	25°C	11.2			mΩ
			–40°C to 85°C	18		mΩ	
			–40°C to 125°C	25		mΩ	
		VIN = 0.8 V	25°C	10			mΩ
			–40°C to 85°C	16		mΩ	
			–40°C to 125°C	23		mΩ	
V _{OL,PG}	Power Good V _{OL}	I _{PG} = 1 mA	–40°C to 125°C	0.2			V
R _{PD,ON}	Smart Pull Down Resistance	ON < V _{IL}	25°C	500			kΩ
			–40°C to 125°C	1000		kΩ	
R _{QOD}	QOD Resistance	ON < V _{IL}	25°C	25			Ω
			–40°C to 125°C	100		Ω	
Protection							
I _{SC,H}	Short Circuit Current Limit (High)	V _{OUT} ≤ V _{IN} - 1.5 V	–40°C to 125°C	10			A
I _{SC,L}	Short Circuit Current Limit (Low)	V _{OUT} ≤ V _{SC}	–40°C to 125°C	1.5			A
t _{SC}	Short Circuit Response Time	V _{IN} = 1 V to 5.5 V	–40°C to 125°C	5			μs
V _{SC}	Short Circuit Detection Threshold	VOUT voltage level, rising	–40°C to 125°C	0.45			V
		VOUT voltage level, falling	–40°C to 125°C	0.35		V	
TSD	Thermal Shutdown		-	170			°C
TSD _{HYS}	Thermal Shutdown Hysteresis		-	20			°C

7.8 Switching Characteristics (VBIAS = 5 V)

Over operating free-air temperature range (unless otherwise noted). Typical values are at $T_A = 25^\circ\text{C}$.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
VIN = 5V						
t_{ON}	Turn ON time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $C_T = 1000\ \text{pF}$		1980		μs
t_{RISE}	Rise time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $C_T = 1000\ \text{pF}$		1430		μs
t_D	Delay time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $C_T = 1000\ \text{pF}$		554		μs
t_{FALL}	Fall time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $C_T = 1000\ \text{pF}$		224		μs
t_{OFF}	Turn OFF time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $C_T = 1000\ \text{pF}$		15.3		μs

7.8 Switching Characteristics (VBIAS = 5 V) (continued)

Over operating free-air temperature range (unless otherwise noted). Typical values are at $T_A = 25^\circ\text{C}$.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
VIN = 3.3V						
t_{ON}	Turn ON time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $CT = 1000\ \text{pF}$		1480		μs
t_{RISE}	Rise time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $CT = 1000\ \text{pF}$		962		μs
t_D	Delay time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $CT = 1000\ \text{pF}$		517		μs
t_{FALL}	Fall time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $CT = 1000\ \text{pF}$		218		μs
t_{OFF}	Turn OFF time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $CT = 1000\ \text{pF}$		14.8		μs
VIN = 1.8V						
t_{ON}	Turn ON time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $CT = 1000\ \text{pF}$		1040		μs
t_{RISE}	Rise time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $CT = 1000\ \text{pF}$		553		μs
t_D	Delay time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $CT = 1000\ \text{pF}$		489		μs
t_{FALL}	Fall time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $CT = 1000\ \text{pF}$		220		μs
t_{OFF}	Turn OFF time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $CT = 1000\ \text{pF}$		15.2		μs
VIN = 1.2V						
t_{ON}	Turn ON time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $CT = 1000\ \text{pF}$		862		μs
t_{RISE}	Rise time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $CT = 1000\ \text{pF}$		386		μs
t_D	Delay time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $CT = 1000\ \text{pF}$		476		μs
t_{FALL}	Fall time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $CT = 1000\ \text{pF}$		221		μs
t_{OFF}	Turn OFF time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $CT = 1000\ \text{pF}$		15.5		μs
VIN = 0.8V						
t_{ON}	Turn ON time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $CT = 1000\ \text{pF}$		743		μs
t_{RISE}	Rise time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $CT = 1000\ \text{pF}$		282		μs
t_D	Delay time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $CT = 1000\ \text{pF}$		462		μs
t_{FALL}	Fall time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $CT = 1000\ \text{pF}$		222		μs
t_{OFF}	Turn OFF time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $CT = 1000\ \text{pF}$		16.4		μs

7.9 Switching Characteristics (VBIAS = 3.3 V)

Over operating free-air temperature range (unless otherwise noted). Typical values are at $T_A = 25^\circ\text{C}$.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
VIN = 3.3V						
t_{ON}	Turn ON time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $CT = 1000\ \text{pF}$		1560		μs
t_{RISE}	Rise time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $CT = 1000\ \text{pF}$		1010		μs
t_D	Delay time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $CT = 1000\ \text{pF}$		547		μs
t_{FALL}	Fall time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $CT = 1000\ \text{pF}$		224		μs
t_{OFF}	Turn OFF time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $CT = 1000\ \text{pF}$		14.1		μs
VIN = 1.8V						
t_{ON}	Turn ON time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $CT = 1000\ \text{pF}$		1090		μs
t_{RISE}	Rise time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $CT = 1000\ \text{pF}$		581		μs
t_D	Delay time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $CT = 1000\ \text{pF}$		505		μs
t_{FALL}	Fall time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $CT = 1000\ \text{pF}$		223		μs
t_{OFF}	Turn OFF time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $CT = 1000\ \text{pF}$		15.1		μs
VIN = 1.2V						
t_{ON}	Turn ON time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $CT = 1000\ \text{pF}$		903		μs
t_{RISE}	Rise time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $CT = 1000\ \text{pF}$		406		μs
t_D	Delay time	$R_L = 10\ \Omega$, $C_L = 10\ \mu\text{F}$, $CT = 1000\ \text{pF}$		498		μs

7.9 Switching Characteristics (VBIAS = 3.3 V) (continued)

Over operating free-air temperature range (unless otherwise noted). Typical values are at TA = 25°C.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _{FALL}	Fall time	R _L = 10 Ω, C _L = 10 uF, CT = 1000 pF		223		us
t _{OFF}	Turn OFF time	R _L = 10 Ω, C _L = 10 uF, CT = 1000 pF		15.3		us
VIN = 0.8V						
t _{ON}	Turn ON time	R _L = 10 Ω, C _L = 10 uF, CT = 1000 pF		774		us
t _{RISE}	Rise time	R _L = 10 Ω, C _L = 10 uF, CT = 1000 pF		284		us
t _D	Delay time	R _L = 10 Ω, C _L = 10 uF, CT = 1000 pF		489		us
t _{FALL}	Fall time	R _L = 10 Ω, C _L = 10 uF, CT = 1000 pF		222		us
t _{OFF}	Turn OFF time	R _L = 10 Ω, C _L = 10 uF, CT = 1000 pF		15.1		us

7.10 Switching Characteristics (VBIAS = 1.5 V)

Over operating free-air temperature range (unless otherwise noted). Typical values are at TA = 25°C.

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
VIN = 1.5V						
t _{ON}	Turn ON time	R _L = 10 Ω, C _L = 10 uF, CT = 1000 pF		1040		us
t _{RISE}	Rise time	R _L = 10 Ω, C _L = 10 uF, CT = 1000 pF		501		us
t _D	Delay time	R _L = 10 Ω, C _L = 10 uF, CT = 1000 pF		542		us
t _{FALL}	Fall time	R _L = 10 Ω, C _L = 10 uF, CT = 1000 pF		225		us
t _{OFF}	Turn OFF time	R _L = 10 Ω, C _L = 10 uF, CT = 1000 pF		13.4		us
VIN = 1.2V						
t _{ON}	Turn ON time	R _L = 10 Ω, C _L = 10 uF, CT = 1000 pF		959		us
t _{RISE}	Rise time	R _L = 10 Ω, C _L = 10 uF, CT = 1000 pF		421		us
t _D	Delay time	R _L = 10 Ω, C _L = 10 uF, CT = 1000 pF		538		us
t _{FALL}	Fall time	R _L = 10 Ω, C _L = 10 uF, CT = 1000 pF		221		us
t _{OFF}	Turn OFF time	R _L = 10 Ω, C _L = 10 uF, CT = 1000 pF		13.9		us
VIN = 0.8V						
t _{ON}	Turn ON time	R _L = 10 Ω, C _L = 10 uF, CT = 1000 pF		840		us
t _{RISE}	Rise time	R _L = 10 Ω, C _L = 10 uF, CT = 1000 pF		314		us
t _D	Delay time	R _L = 10 Ω, C _L = 10 uF, CT = 1000 pF		526		us
t _{FALL}	Fall time	R _L = 10 Ω, C _L = 10 uF, CT = 1000 pF		218		us
t _{OFF}	Turn OFF time	R _L = 10 Ω, C _L = 10 uF, CT = 1000 pF		14.8		us

7.11 Typical Characteristics

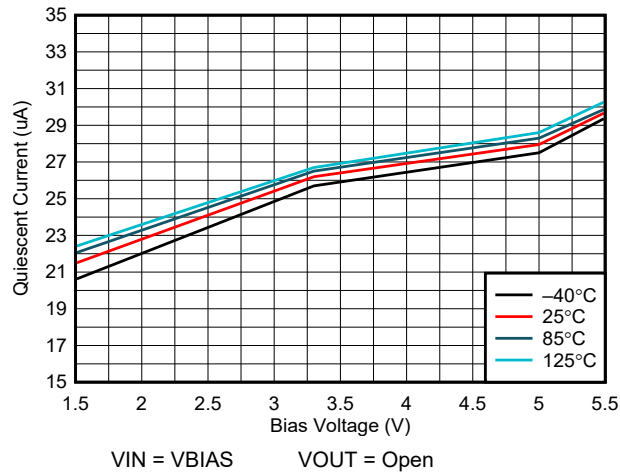


Figure 7-1. Quiescent Current vs Bias Voltage

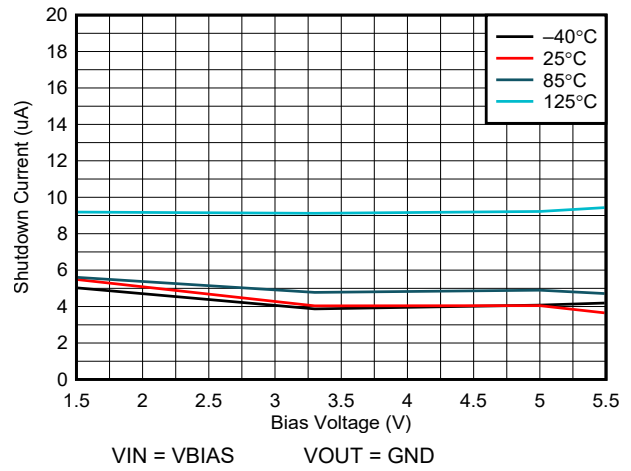


Figure 7-2. VBIAS Shutdown Current vs Bias Voltage

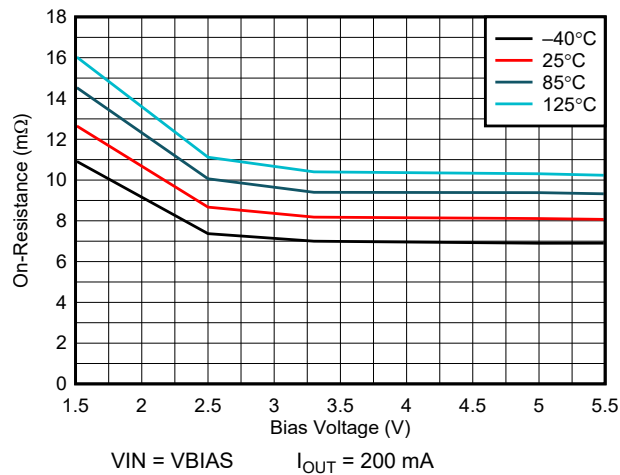


Figure 7-3. ON-Resistance vs Bias Voltage

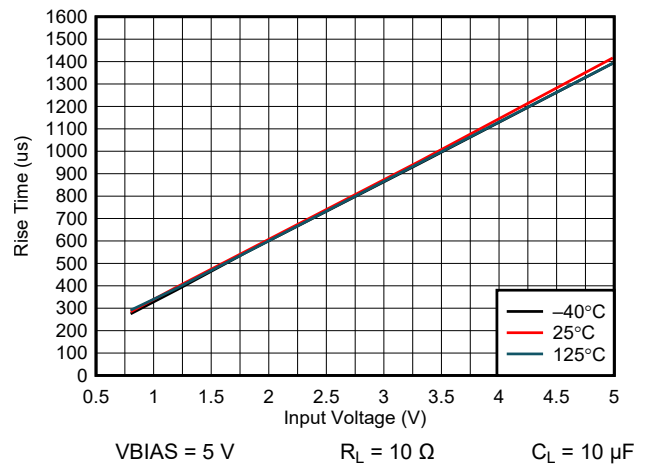


Figure 7-4. Rise Time vs Input Voltage

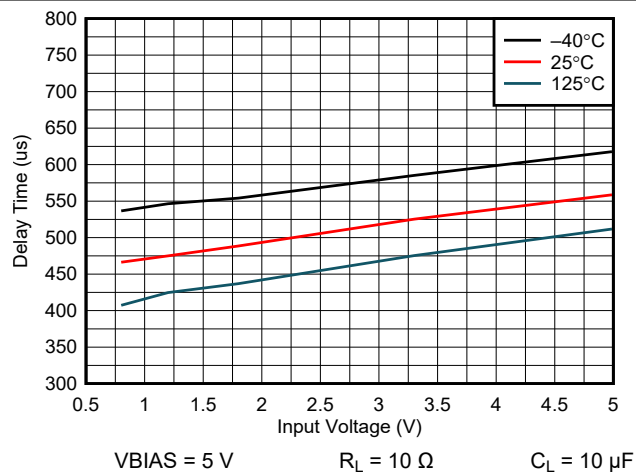


Figure 7-5. Delay Time vs Input Voltage

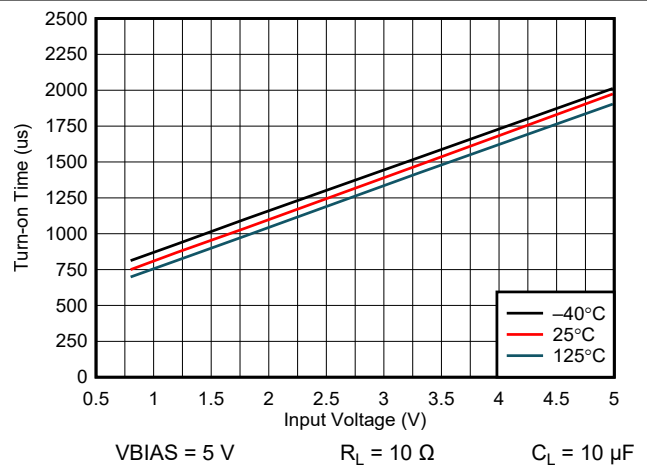


Figure 7-6. Turn-On Time vs Input Voltage

7.11 Typical Characteristics (continued)

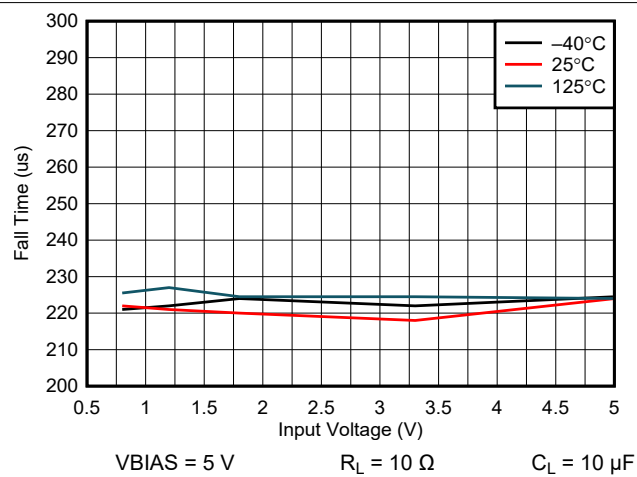


Figure 7-7. Fall Time vs Input Voltage

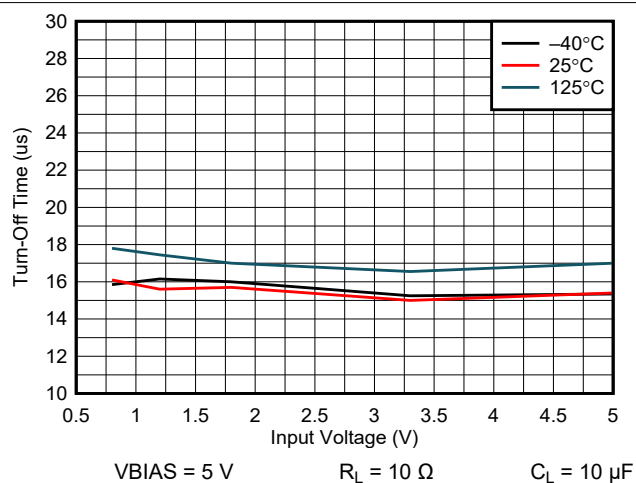


Figure 7-8. Turn-Off Time vs Input Voltage

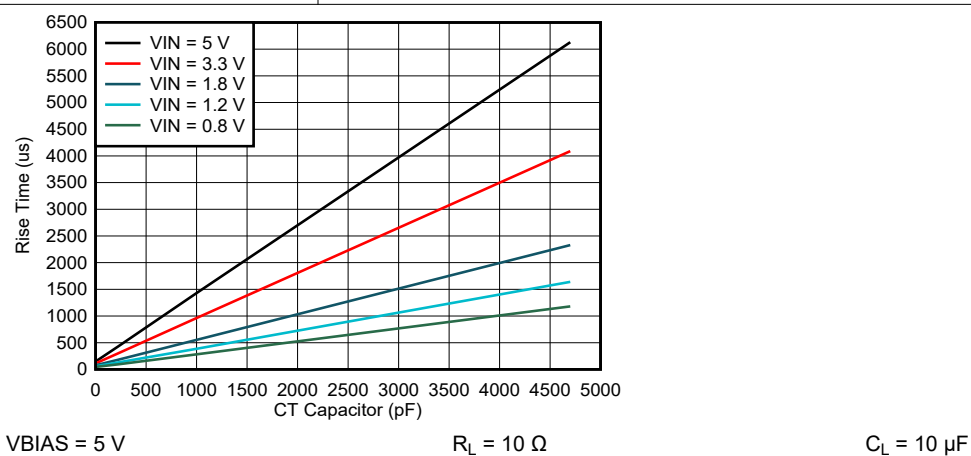
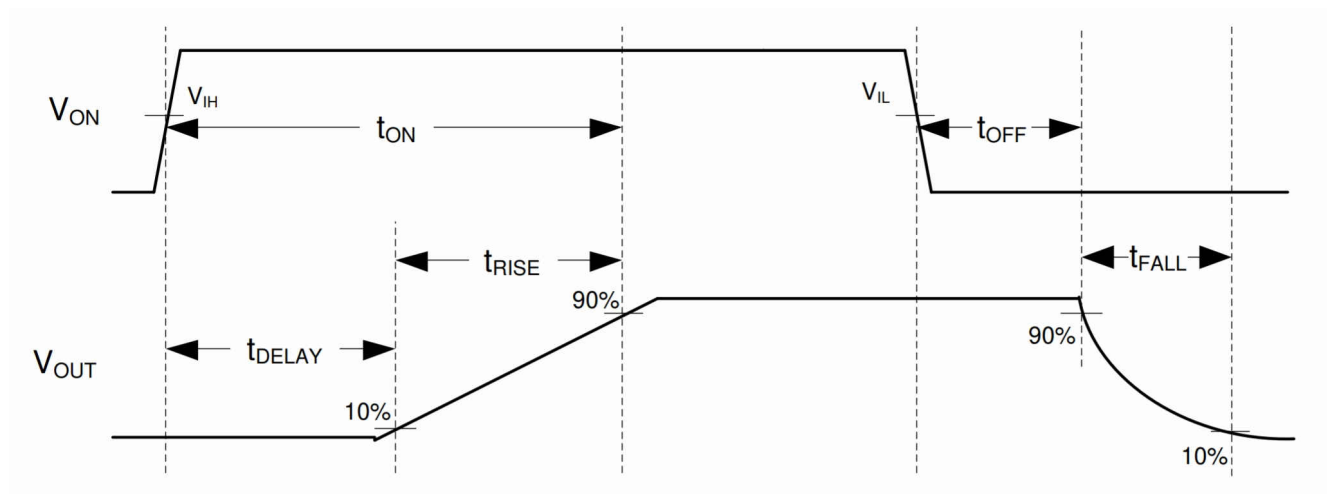


Figure 7-9. Rise Time vs CT Capacitance

8 Timing Diagram



8-1. TPS22992x Timing Parameters

9 Detailed Description

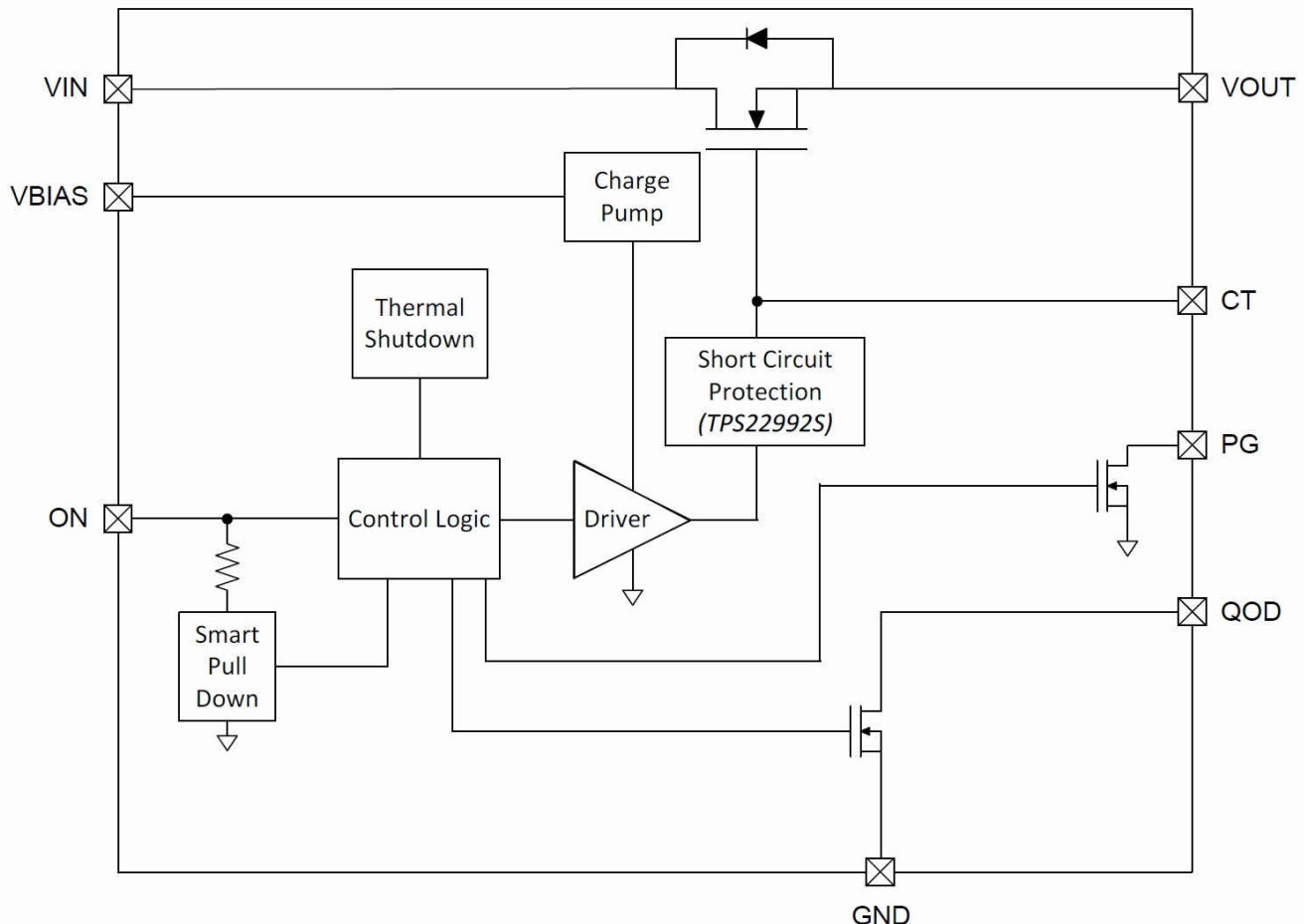
9.1 Overview

The TPS22992 and TPS22992S devices are both single-channel load switches with an 8.7-m Ω power MOSFET designed to operate up to 6 A. The voltage range of the TPS22992 device is 0.1 V to 5.5 V, and the voltage range of the TPS22992S device is 1 V to 5.5 V. A configurable rise time provides flexibility for power sequencing and minimizes inrush current for high capacitance loads.

The switch is controlled by an enable pin (ON), which is capable of interfacing directly with low voltage GPIO signals down to its V_{IH} level of 0.8 V. The TPS22992x device has an optional QOD pin for quick output discharge when switch is turned off, and the fall time (t_{FALL}) of the output can be adjusted through an external resistor. There is a Power Good (PG) signal on the device that indicates when the main MOSFET is fully turned on and the on-resistance is at its final value.

Both TPS22992x devices come with thermal shutdown to ensure protection in high temperature environments. The TPS22992S also integrates overcurrent protection, preventing damage to the device if the output is shorted to ground during operation or start-up.

9.2 Functional Block Diagram



9.3 Feature Description

9.3.1 ON and OFF Control

The ON pin controls the state of the switch. The ON pin is compatible with standard GPIO logic threshold so it can be used in a wide variety of applications. When power is first applied to VIN, a Smart Pulldown is used to keep the ON pin from floating until the system sequencing is complete. After the ON pin is deliberately driven high ($\geq V_{IH}$), the Smart Pulldown is disconnected to prevent unnecessary power loss. See the below table when the ON Pin Smart Pulldown is active.

ON Pin Voltage	ON Pin Function
$\leq V_{IL}$	Pulldown active
$\geq V_{IH}$	No pulldown

9.3.2 Adjustable Quick Output Discharge

The TPS22992x device includes a QOD feature that can be configured in one of three ways:

- QOD pin shorted to VOUT pin. Using this method, the discharge rate after the switch becomes disabled is controlled with the value of the internal resistance RQOD. The value of this resistance is listed in the Electrical Characteristics table.
- QOD pin connected to VOUT pin using an external resistor REXT. After the switch becomes disabled, the discharge rate is controlled by the value of the total resistance of the QOD.
- QOD pin is unused and left floating. Using this method, there is no quick output discharge functionality, and the output remains floating after the switch is disabled.

Fall time is dependent on the strength of the configured pulldown resistance on the output.

9.3.3 Adjustable Slew Rate

A capacitor to GND on the CT pin sets the slew rate, and the higher the capacitance the lower the slew rate. The voltage on the CT pin can be as high as 15 V; therefore, the minimum voltage rating for the CT capacitor must be 30 V for optimal performance. Rise times for VBIAS = 5 V are shown below.

CT Capacitor	VIN = 5 V	VIN = 3.3 V	VIN = 1.8 V	VIN = 1.2 V	VIN = 0.8 V
0 pF	147 μ s	113 μ s	77 μ s	59 μ s	45 μ s
220 pF	426 μ s	297 μ s	179 μ s	129 μ s	94 μ s
1000 pF	1430 μ s	962 μ s	553 μ s	386 μ s	282 μ s
4700 pF	6130 μ s	4090 μ s	2330 μ s	1640 μ s	1180 μ s

The following equation can be used to estimate the rise time for different VIN and CT capacitors at VBIAS = 5 V.

$$t_R = V_{IN} \times (0.27 \times CT + 25.5) + 24.9 \quad (1)$$

Where:

- t_R = Rise time in μ s
- V_{IN} = Input voltage in V
- CT = CT capacitance in pF

9.3.4 Power Good (PG) Signal

The TPS22992x device has a Power Good (PG) output signal to indicate the gate of the pass FET is driven high and the switch is on with the on-resistance close to its final value (full load ready). The signal is an active high and open drain output which can be connected to a voltage source through an external pullup resistor, R_{PU} . This voltage source can be VOUT from the TPS22992x device or another external voltage. VBIAS is required for PG to have a valid output.

9.3.5 Thermal Shutdown

When the device temperature reaches 170°C (typical), the device shuts itself off to prevent thermal damage. After the device cools off by about 20°C, it turns back on. If the device is kept in a thermally stressful environment, then the device oscillates between these two states until it can keep its temperature below the thermal shutdown point.

9.3.6 Short Circuit Protection (TPS22992S)

The device limits current to the output in case of output shorts. When a short occurs, the large V_{IN} to V_{OUT} voltage drop causes the switch to limit the output current (I_{SC}). When the output is below the short circuit threshold (V_{SC}), a lower limit is used to minimize the power dissipation while the fault is present. The device continues to limit the current until it reaches its thermal shutdown temperature. At this time, the device turns off until its temperature has lowered by the thermal hysteresis (20°C typical) before turning on again.

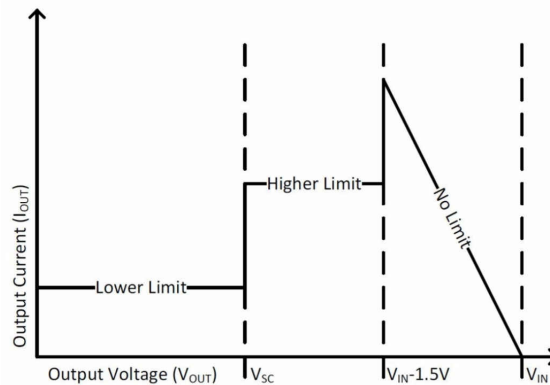


FIG 9-1. Output Short Circuit Current Limiting

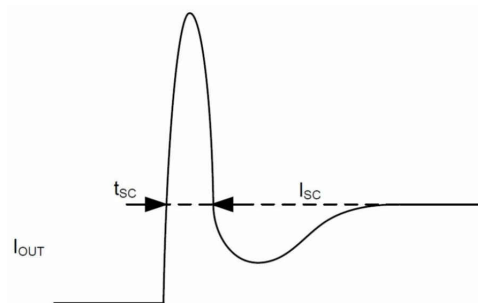


FIG 9-2. Output Short Circuit Response

9.4 Device Functional Modes

The below table summarizes the device functional modes.

ON	Fault Condition	V _{OUT} State
L	N/A	Hi-Z
H	None	V_{IN} (through R_{ON})
H	Output short	Current limited (TPS22992S)
X	Thermal shutdown	Hi-Z

10 Application and Implementation

Note

以下のアプリケーション情報は、TI の製品仕様に含まれるものではなく、TI ではその正確性または完全性を保証いたしません。個々の目的に対する製品の適合性については、お客様の責任で判断していただくことになります。お客様は自身の設計実装を検証しテストすることで、システムの機能を確認する必要があります。

10.1 Application Information

This section highlights some of the design considerations when implementing this device in various applications.

10.2 Typical Application

This typical application demonstrates how the TPS22992x device can be used to limit start-up inrush current.

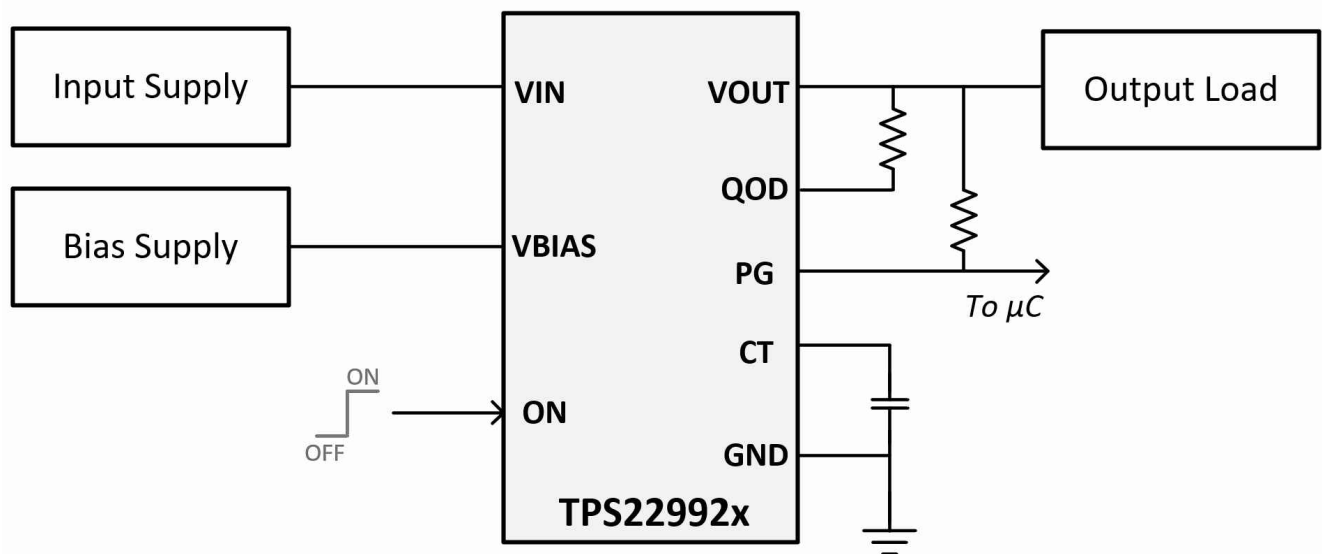


図 10-1. TPS22992x Typical Application

10.2.1 Design Requirements

For this example, the values below are used as the design parameters.

表 10-1. Design Parameters

PARAMETER	VALUE
V_{BIAS}	5 V
V_{IN}	5 V
C_L	47 μ F
Maximum acceptable inrush current	200 mA

10.2.2 Detailed Design Procedure

When the switch is enabled, the output capacitance must be charged up from 0 V to the set value (5 V in this example). This charge arrives in the form of inrush current. Inrush current can be calculated using the equation below.

$$\text{Inrush Current} = C_L \times dV_{OUT}/dt \quad (2)$$

Where:

- C_L is the output capacitance.
- dV_{OUT} is the change in V_{OUT} during the ramp up of the output voltage when device is enabled.
- dt is the rise time in V_{OUT} during the ramp up of the output voltage when the device is enabled.

The TPS22992 offers an adjustable rise time for V_{OUT} , allowing the user to control the inrush current during turn-on. The appropriate rise time can be calculated using the design requirements and the inrush current equation as shown below.

$$200 \text{ mA} = 47 \text{ } \mu\text{F} \times 5 \text{ V}/dt \quad (3)$$

$$dt = 1175 \text{ } \mu\text{s} \quad (4)$$

To ensure an inrush current of less than 200 mA, a C_T value that yields a rise time of more than 1175 μs must be chosen. See the oscilloscope captures in the [Application Performance Plots](#) section for an example of how the C_T capacitor can be used to reduce inrush current.

10.2.3 Application Performance Plots

The below oscilloscope captures show the difference between the inrush current for $C_T = 0 \text{ pF}$ and $C_T = 1000 \text{ pF}$ settings. The $C_T = 1000 \text{ pF}$ setting is able to keep the inrush current under the required 200 mA, while the $C_T = 0 \text{ pF}$ setting is too fast for this design.

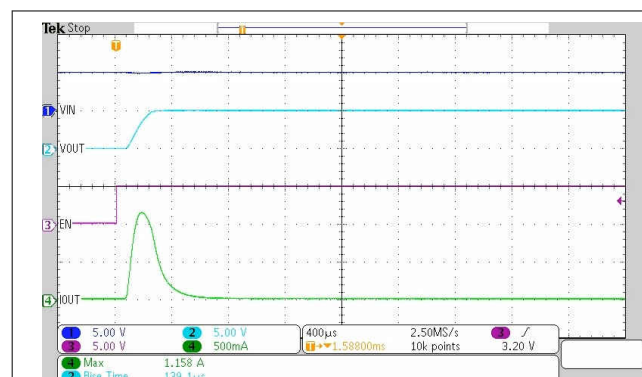


Figure 10-2. Inrush Current for $C_L = 47 \text{ } \mu\text{F}$ with $C_T = 0 \text{ pF}$

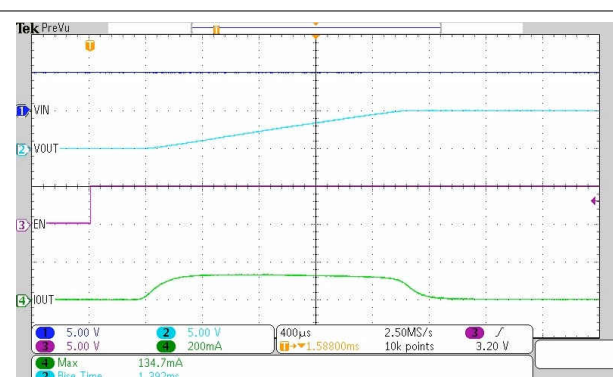


Figure 10-3. Inrush Current for $C_L = 47 \text{ } \mu\text{F}$ with $C_T = 1000 \text{ pF}$

11 Power Supply Recommendations

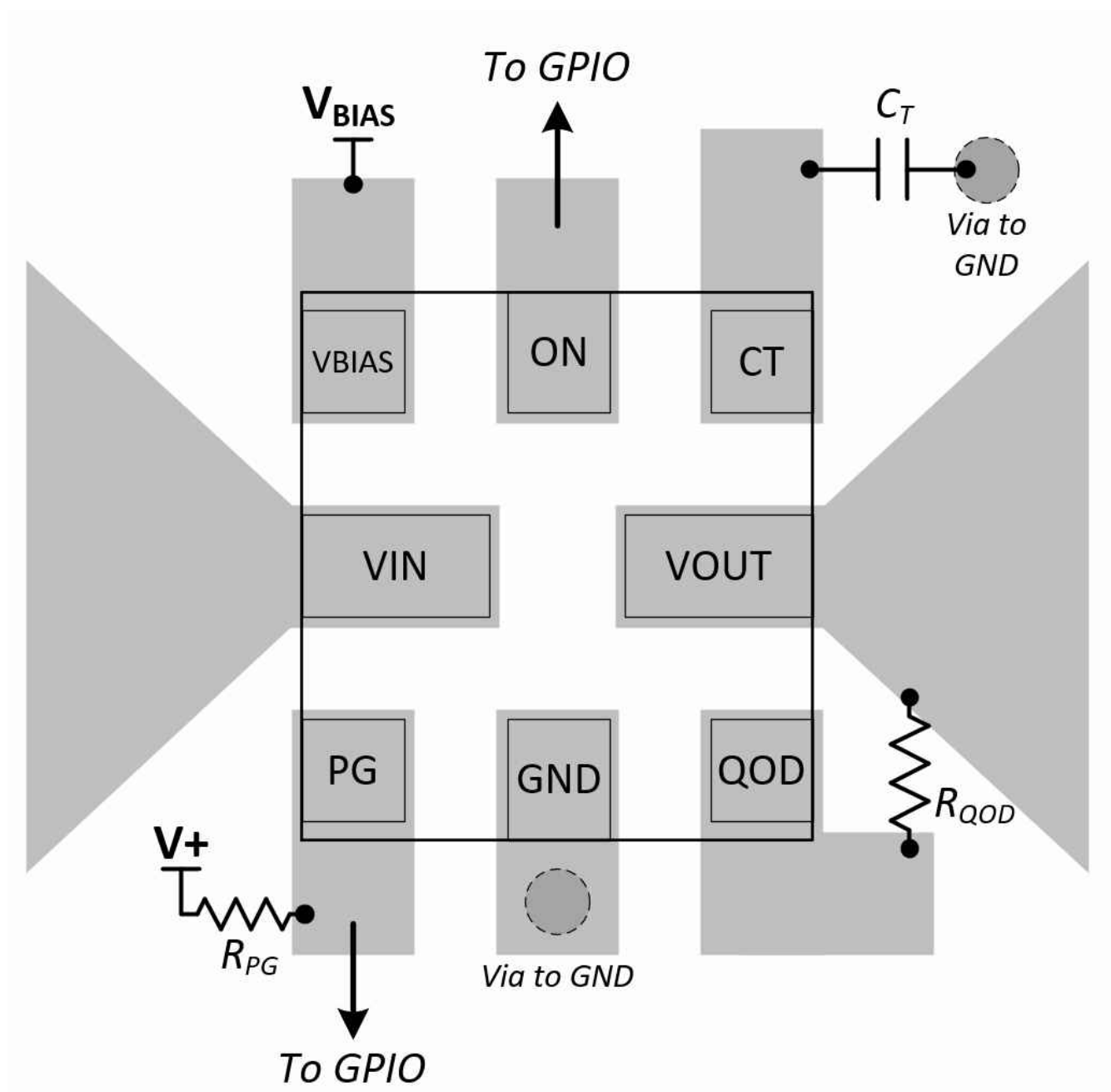
The TPS22992 device is designed to operate with a VIN range of 0.1 V to 5.5 V, and the TPS22992S device over a range of 1 V to 5.5 V. The VIN power supply must be well regulated and placed as close to the device terminal as possible. The power supply must be able to withstand all transient load current steps. In most situations, using an input capacitance (C_{IN}) of 1 μ F is sufficient to prevent the supply voltage from dipping when the switch is turned on. In cases where the power supply is slow to respond to a large transient current or large load current step, additional bulk capacitance can be required on the input.

12 Layout

12.1 Layout Guidelines

For best performance, all traces must be as short as possible. To be most effective, the input and output capacitors must be placed close to the device to minimize the effects that parasitic trace inductances can have on normal operation. Using wide traces for VIN, VOUT, and GND helps minimize the parasitic electrical effects.

12.2 Layout Example



✎ 12-1. TPS22992x Layout Example

13 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

13.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on [ti.com](https://www.ti.com). Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

13.2 サポート・リソース

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13.3 Trademarks

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13.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

13.5 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

14 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
TPS22992RXPR	Active	Production	WQFN-HR (RXP) 8	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	MC
TPS22992RXPR.A	Active	Production	WQFN-HR (RXP) 8	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	MC
TPS22992SRXNR	Active	Production	WQFN-HR (RXN) 8	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	MB
TPS22992SRXNR.A	Active	Production	WQFN-HR (RXN) 8	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	MB

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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